

## **TDA7384A**

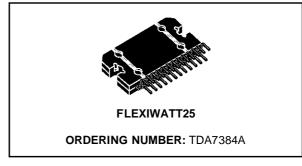
## 4 x 25W FOUR BRIDGE CHANNELS CAR RADIO AMPLIFIER

**ADVANCE DATA** 

- HIGH OUTPUT POWER CAPABILITY:  $4 \times 35 \text{W max.}/4\Omega \text{ EIAJ}$   $4 \times 25 \text{W}/4\Omega$  @ 14.4V, 1KHz, 10%  $4 \times 21 \text{W}/4\Omega$  @ 13.2V, 1KHz, 10%
- LOW DISTORTION
- LOW OUTPUT NOISE
- ST-BY FUNCTION
- MUTE FUNCTION
- AUTOMUTE AT MIN. SUPPLY VOLTAGE DE-TECTION
- LOW EXTERNAL COMPONENT COUNT:
  - INTERNALLY FIXED GAIN (26dB)
  - NO EXTERNAL COMPENSATION
  - NO BOOTSTRAP CAPACITORS

### **PROTECTIONS:**

- OUTPUT SHORT CIRCUIT TO GND, TO V<sub>S</sub>, ACROSS THE LOAD
- VERY INDUCTIVE LOADS
- OVERRATING CHIP TEMPERATURE WITH SOFT THERMAL LIMITER
- LOAD DUMP VOLTAGE
- FORTUITOUS OPEN GND



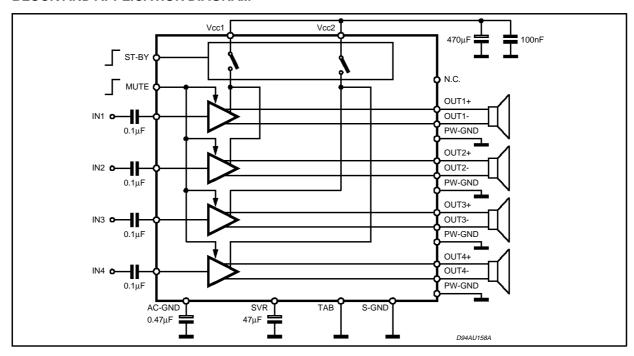
- REVERSED BATTERY
- ESD

#### **DESCRIPTION**

The TDA7384A is a new technology class AB Audio Power Amplifier in Flexiwatt 25 package designed for high end car radio applications.

Thanks to the fully complementary PNP/NPN output configuration the TDA7384A allows a rail to rail output voltage swing with no need of bootstrap capacitors. The extremely reduced components count allows very compact sets.

#### **BLOCK AND APPLICATION DIAGRAM**

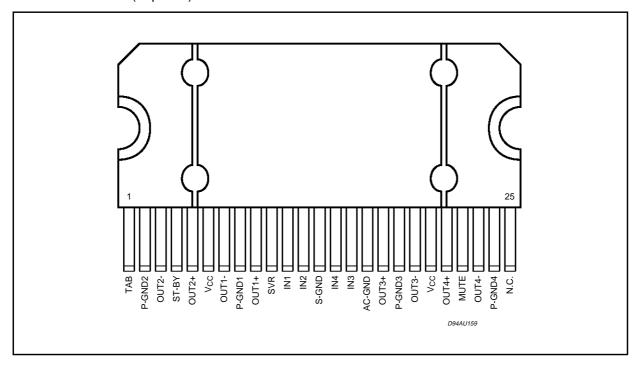


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## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vcc	Operating Supply Voltage	18	V
V <sub>CC (DC)</sub>	DC Supply Voltage	28	V
V <sub>CC (pk)</sub>	Peak Supply Voltage (t = 50ms)	50	V
lo	Output Peak Current: Repetitive (Duty Cycle 10% at f = 10Hz) Non Repetitive (t = 100µs)	4.5 5.5	A A
P <sub>tot</sub>	Power dissipation, (T <sub>case</sub> = 70°C)	80	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	– 55 to 150	°C

## **PIN CONNECTION** (Top view)



## THERMAL DATA

Symbol	Parameter	Value	Unit
R <sub>th j-case</sub>	Thermal Resistance Junction to Case Max.	1	°C/W



# **ELECTRICAL CHARACTERISTICS** ( $V_S = 14.4V$ ; f = 1KHz; $R_g = 600\Omega$ ; $R_L = 4\Omega$ ; $T_{amb} = 25^{\circ}C$ ; Refer to the test and application diagram, unless otherwise specified.)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
I <sub>q1</sub>	Quiescent Current	R <sub>L</sub> = ∞	120	190	270	mA
Vos	Output Offset Voltage	Play Mode			±80	mV
dV <sub>OS</sub>	During mute ON/OFF output offset voltage				±80	mV
Gv	Voltage Gain		25	26	27	dB
dG√	Channel Gain Unbalance				±1	dB
Po	Output Power	V <sub>S</sub> = 13.2V; THD = 10% V <sub>S</sub> = 13.2V; THD = 0.8% V <sub>S</sub> = 14,4V; THD = 10%	19 14	21 17 26		W W W
P <sub>O max</sub>	Max. Output Power	EIAJ RULES $V_S = 13.7V$ $V_i = 5V rms$	32	35	-	W
THD	Distortion	$P_0 = 4W$		0.04	0.15	%
e <sub>No</sub>	Output Noise	"A Weighted" Bw = 20Hz to 20KHz		50 70	70 100	μV μV
SVR	Supply Voltage Rejection	$f = 100Hz; V_r = 1Vrms$	50	65		dB
f <sub>ch</sub>	High Cut-Off Frequency	$P_{O} = 0.5W$	100	200		KHz
Ri	Input Impedance		70	100		ΚΩ
Ст	Cross Talk	$f = 1KHz$ $P_O = 4W$ $f = 10KHz$ $P_O = 4W$	60	70 60	1 1	dB dB
I <sub>SB</sub>	St-By Current Consumption	$V_{St-By} = 1.5V$			100	μΑ
$I_{pin4}$	St-by pin Current	VSt-By = 1.5V to 3.5V			±10	μΑ
V <sub>SB out</sub>	St-By Out Threshold Voltage	(Amp: ON)	3.5			V
V <sub>SB in</sub>	St-By in Threshold Voltage	(Amp: OFF)			1.5	V
A <sub>M</sub>	Mute Attenuation	P <sub>Oref</sub> = 4W	80	90		dB
V <sub>M out</sub>	Mute Out Threshold Voltage	(Amp: Play)	3.5			V
$V_{M in}$	Mute In Threshold Voltage	(Amp: Mute)			1.5	V
V <sub>AM</sub> in	V <sub>S</sub> Automute Threshold	(Amp: Mute) Att ≥ 80dB; P <sub>Oref</sub> = 4W (Amp: Play) Att < 0.1dB; P <sub>O</sub> = 0.5W		7.6	6.5 8.5	V V
I <sub>pin22</sub>	Muting Pin Current	V <sub>MUTE</sub> = 1.5V to 3.5W (Sourced Current)	5	11	20	μΑ

Figure 1: Standard Test and Application Circuit

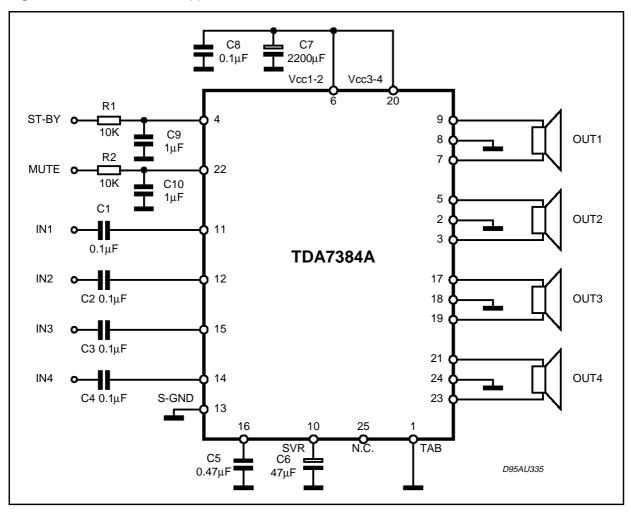


Figure 2: P.C.B. and component layout of the figure 1 (1:1 scale)

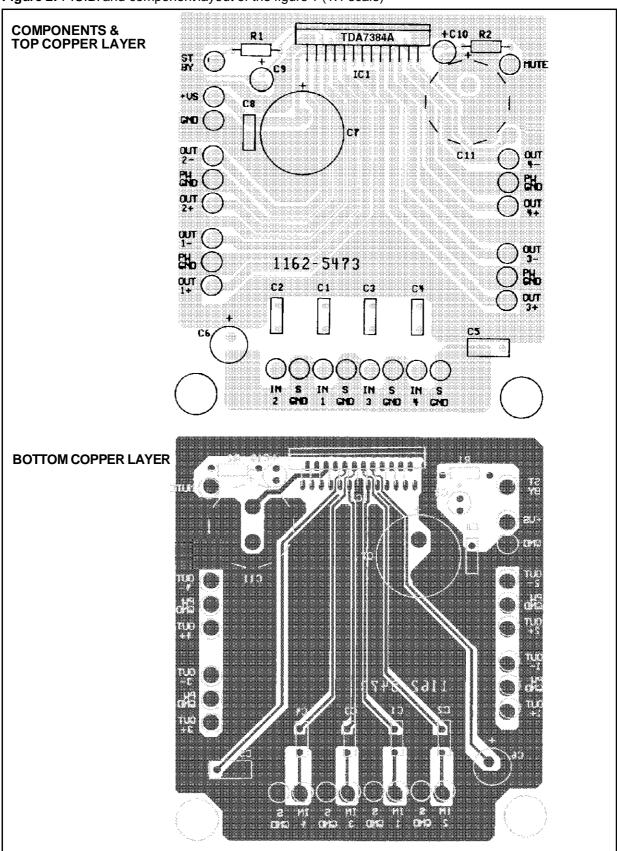


Figure 3: Quiescent Current vs. Supply Voltage

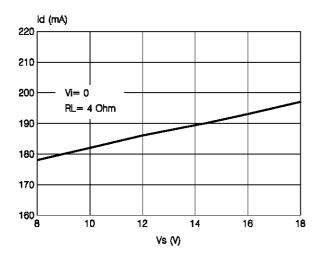


Figure 5: Output Power vs. Supply Voltage

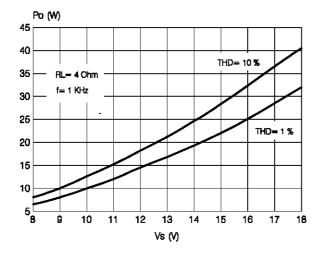


Figure 7: Distortion vs. Frequency

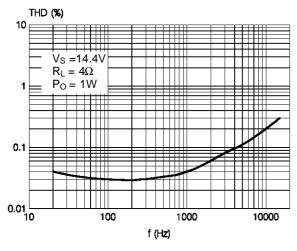


Figure 4: Quiescent Output Voltage vs. Supply Voltage

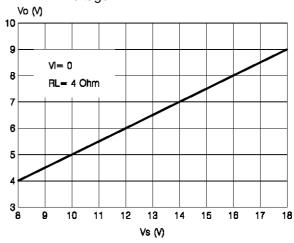
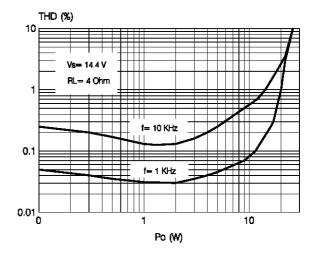
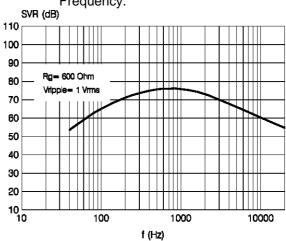


Figure 6: Distortion vs. Output Power

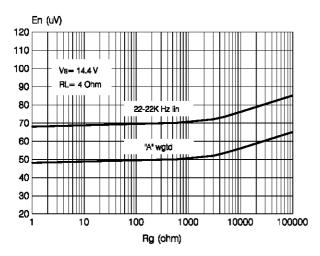


**Figure 8:** Supply Voltage Rejection vs. Frequency.



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Figure 9: Output Noise vs. Source Resistance



# **APPLICATION HINTS** (ref. to the circuit of fig. 1) SVR

Besides its contribution to the ripple rejection, the SVR capacitor governs the turn ON/OFF time sequence and, consequently, plays an essential role in the pop optimization during ON/OFF transients. To conveniently serve both needs, **ITS MINIMUM RECOMMENDED VALUE IS 10**µF.

### **INPUT STAGE**

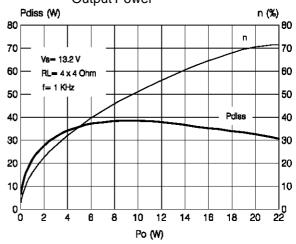
The TDA7384A's inputs are ground-compatible and can stand very high input signals (± 8Vpk) without any performances degradation.

If the standard value for the input capacitors (0.1 $\mu$ F) is adopted, the low frequency cut-off will amount to 16 Hz.

#### STAND-BY AND MUTING

STAND-BY and MUTING facilities are both CMOS-COMPATIBLE. If unused, a straight connection to Vs of their respective pins would be admissible. Conventional low-power transistors can

**Figure 10:** Power Dissipation & Efficiency vs. Output Power



be employed to drive muting and stand-by pins in absence of true CMOS ports or microprocessors.

R-C cells have always to be used in order to smooth down the transitions for preventing any audible transient noises.

Since a DC current of about 10 uA normally flows out of pin 22, the recommended muting-series resistance (R<sub>2</sub>) is in the range  $70 \text{K}\Omega$  to  $120 \text{K}\Omega$ , which is also sufficiently high to allow a muting capacitor reasonably small (about  $1 \mu \text{F}$ ).

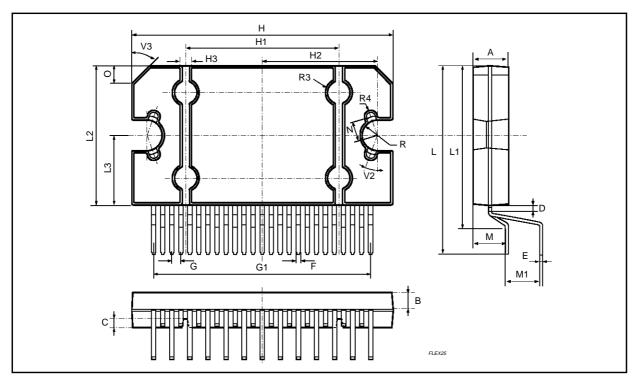
If  $R_2$  values higher than recommended are chosen, the involved risk will be that the voltage at pin 22 may rise to above the 1.5 V threshold voltage and the device will consequently fail to turn OFF when the mute line is brought down.

Conversely, in case of  $R_2$  lower than  $70K\Omega$ , no negative impact will exist other than the necessity to increase  $C_{10}$  if the pop during muting operations grows to unacceptable levels.

About the stand-by, the time constant to be assigned in order to obtain a virtually pop-free transition has to be slower than 2.5V/ms.

## FLEXIWATT25 PACKAGE MECHANICAL DATA

DIM.	mm			inch			
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α	4.45		4.65	0.175		0.183	
В	1.80	1.90	2.00	0.070	0.074	0.079	
С		1.40			0.055		
D	0.75	0.90	1.05	0.029	0.035	0.041	
Е	0.37	0.39	0.42	0.014	0.015	0.016	
F			0.57			0.022	
G	0.80	1.00	1.20	0.031	0.040	0.047	
G1	23.75	24.00	24.25	0.935	0.945	0.955	
Н	28.90	29.23	29.30	1.138	1.150	1.153	
H1		17.00			0.669		
H2		12.80			0.503		
H3		0.80			0.031		
L	21.57	21.97	22.37	0.849	0.865	0.880	
L1	18.57	18.97	19.37	0.731	0.786	0.762	
L2	15.50	15.70	15.90	0.610	0.618	0.626	
L3	7.70	7.85	7.95	0.303	0.309	0.313	
М	3.70	4.00	4.30	0.145	0.157	0.169	
M1	3.60	4.00	4.40	0.142	0.157	0.173	
N		2.20			0.086		
0		2			0.079		
R		1.70			0.067		
R4		0.50			0.019		
V2	20°						
V3	45°						



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